

DIGITRON SEMICONDUCTORS

Bipolar Junction Transistor HR flow

All parts are screened per MIL-PRF-19500, JANTX Level and the device detail specification. All testing is performed at room temperature, unless indicated otherwise. For testing at high and low temperatures, Group A testing is required.

	Test	Method	Conditions / Notes
1	Temperature Cycling	<i>MIL-STD-750 Method 1051</i>	Test condition C or maximum storage temperature, whichever less. 20 cycles, 10 minutes per extreme.
2	Interim Electrical Testing		DC parameters per device detail specification.
3	High Temperature Reverse Bias Burn-in	<i>MIL-STD-750 Method 1039</i>	Condition A. 48 hours at 150°C and 80% of rated V_{CBO} .
4	Interim Electrical Testing		DC parameters per device detail specification.
5	Power Burn-in	<i>MIL-STD-750 Method 1039</i>	Condition B. 160 hours at 25°C with power applied to achieve specified conditions.
6	Final Electrical Testing		DC parameters per device detail specification.
7	Delta Calculation		Delta parameters and limits per device detail specification.
8	PDA Calculation		10 percent defective allowed.
9	Seal Test Fine Leak	<i>MIL-STD-750 Method 1071</i>	Condition G or H
10	Seal Test Gross Leak	<i>MIL-STD-750 Method 1071</i>	Condition C

Notes:

1. Testing varies in accordance with the device detail specification.
2. Specific customer testing needs may be accommodated into any testing flow (selection tests, temperature requirements, special tests).